

Plastic-Encapsulate MOSFETS

N-Channel 20-V(D-S) MOSFET

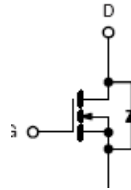
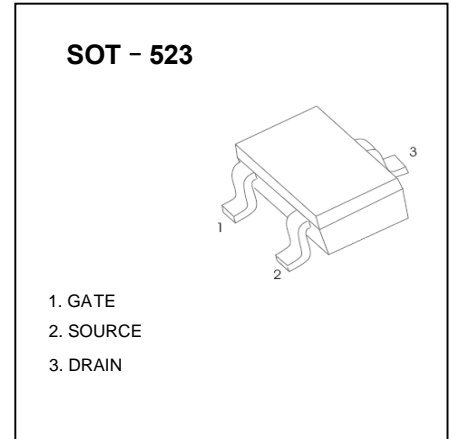
FEATURE

TrenchFET Power MOSFET

APPLICATIONS

- Load Switch for Portable Devices
- DC/DC Converter

MARKING: 2302



Maximum ratings ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 8	
Continuous Drain Current	I_D	2.8	A
Continuous Source-Drain Current(Diode Conduction)	I_S	0.6	
Power Dissipation	P_D	0.35	W
Thermal Resistance from Junction to Ambient ($t \leq 5s$)	$R_{\theta JA}$	357	$^{\circ}\text{C}/\text{W}$
Operating Junction	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55 ~+150	

Electrical characteristics ($T_a=25^\circ\text{C}$ unless otherwise noted)

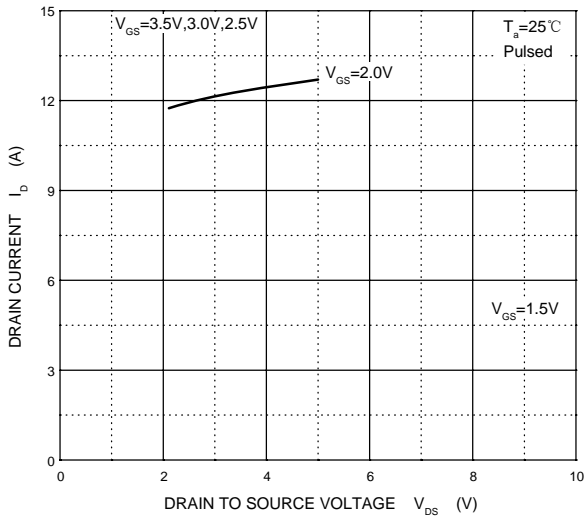
Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 10\mu A$	20			V
Gate-threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 50\mu A$	0.65	0.95	1.2	
Gate-body leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 8V$			± 100	nA
Zero gate voltage drain current	I_{DSS}	$V_{DS} = 20V, V_{GS} = 0V$			1	μA
Drain-source on-resistance ^a	$r_{DS(on)}$	$V_{GS} = 4.5V, I_D = 2.8A$		0.045	0.060	Ω
		$V_{GS} = 2.5V, I_D = 2.0A$		0.070	0.115	
Forward transconductance ^a	g_{fs}	$V_{DS} = 5V, I_D = 2.0A$		8		S
Diode forward voltage	V_{SD}	$I_S = 0.94A, V_{GS} = 0V$		0.76	1.2	V

Notes :

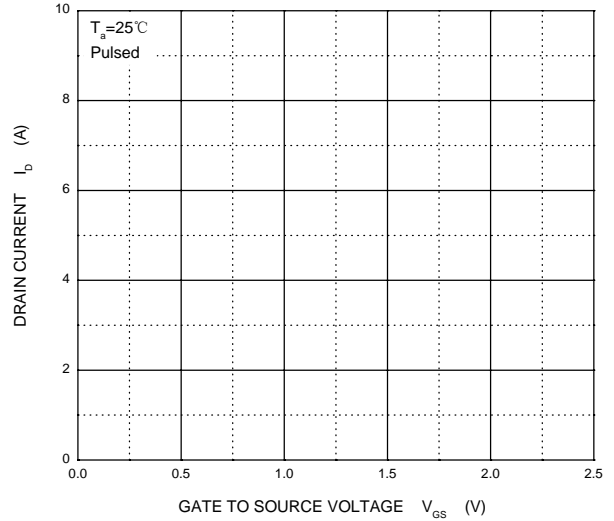
- Pulse Test : Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- These parameters have no way to verify.

Typical Characteristics

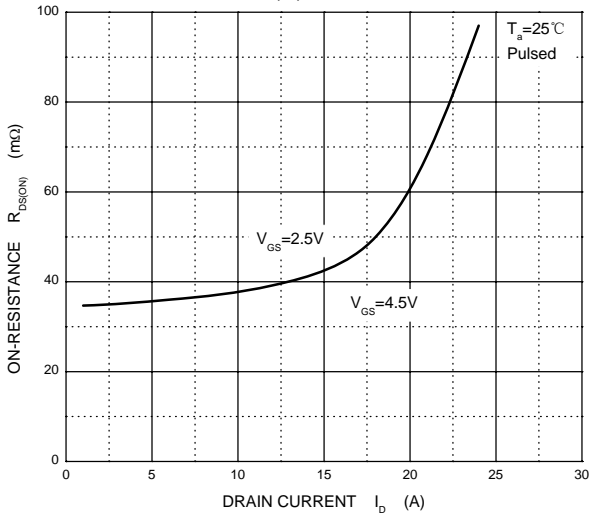
Output Characteristics



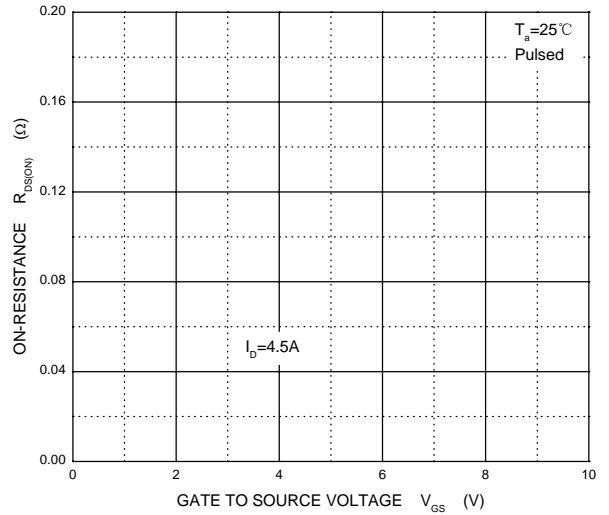
Transfer Characteristics



$R_{DS(ON)}$ — I_D

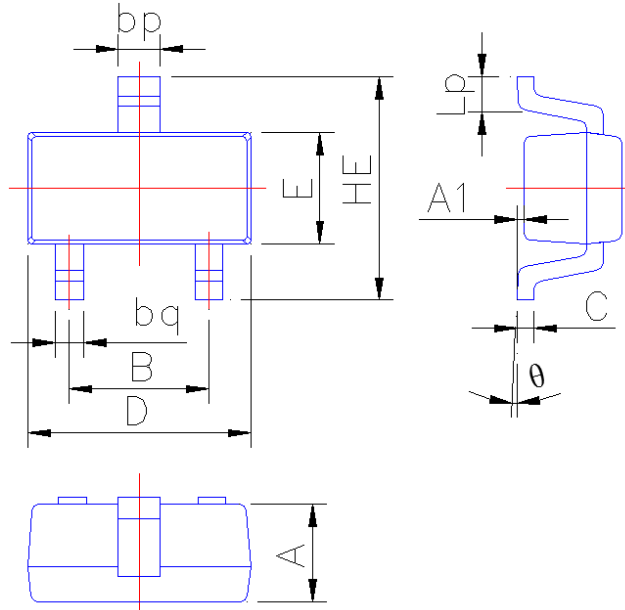


$R_{DS(ON)}$ — V_{GS}





SOT-523 PACKAGE OUTLINE



Symbol	Dimension in Millimeters	
	Min	Max
A	0.60	0.80
A1	0.010	0.100
B	0.95	1.05
bp	0.26	0.40
bq	0.16	0.30
C	0.09	0.15
D	1.50	1.70
E	0.70	0.85
HE	1.45	1.75
Lp	0.16	0.36
θ	0°	5°